

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number:	PMN49EN,135
Manufacturer:	NXP USA Inc.
Package:	Please confirm with sales
Availability:	Please confirm with sales

Product Page:

<https://antrexco.com/product/details/nxp-usa-inc/pmn49en-135.html>

Request a Quote:

[Submit RFQ for this part](#)



Scan for product page

Contact Information

Email: info@antrexco.com

WhatsApp: +86-186-8066-5326

Website: <https://antrexco.com>

Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <http://www.nxp.com>, <http://www.philips.com/> or <http://www.semiconductors.philips.com/>, use **<http://www.nexperia.com>**

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use **salesaddresses@nexperia.com** (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

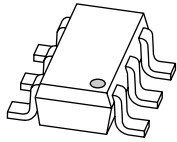
Should be replaced with:

- © **Nexperia B.V. (year). All rights reserved.**

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia



PMN49EN

N-channel TrenchMOS logic level FET

Rev. 01 — 13 April 2007

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology.

1.2 Features

- Logic level threshold
- Fast switching

1.3 Applications

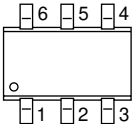
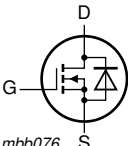
- Battery management
- High-speed switching

1.4 Quick reference data

- $V_{DS} \leq 30\text{ V}$
- $I_D \leq 4.6\text{ A}$
- $R_{DS(on)} \leq 47\text{ m}\Omega$
- $Q_{GD} = 1.6\text{ nC (typ)}$

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1, 2, 5, 6	drain (D)	 SOT457 (TSOP6)	 mbb076
3	gate (G)		
4	source (S)		

3. Ordering information

Table 2. Ordering information

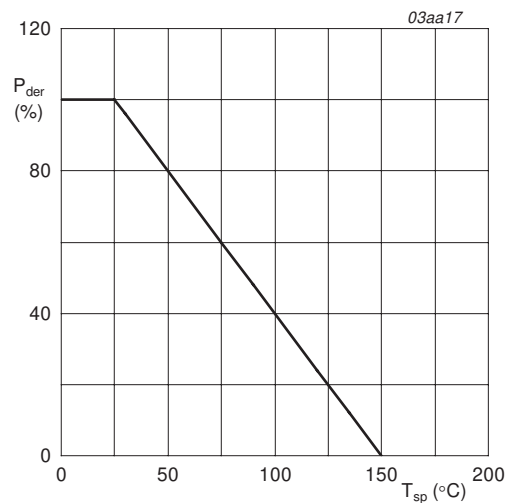
Type number	Package		
	Name	Description	Version
PMN49EN	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Limiting values

Table 3. Limiting values

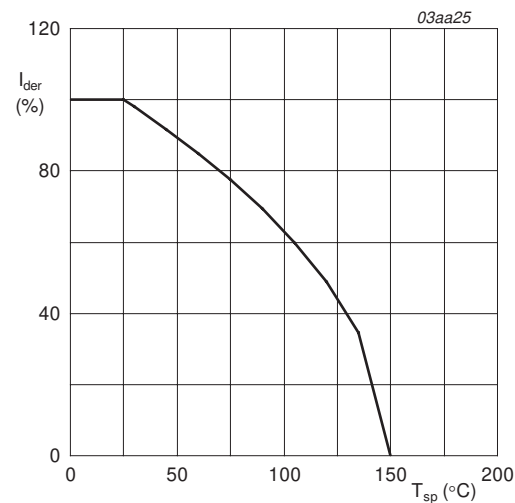
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-	± 20	V
I_D	drain current	$T_{sp} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 2 and 3	-	4.6	A
		$T_{sp} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 2	-	2.9	A
I_{DM}	peak drain current	$T_{sp} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; see Figure 3	-	18.4	A
P_{tot}	total power dissipation	$T_{sp} = 25\text{ °C}$; see Figure 1	-	1.75	W
T_{stg}	storage temperature		-55	+150	°C
T_j	junction temperature		-55	+150	°C
Source-drain diode					
I_S	source current	$T_{sp} = 25\text{ °C}$	-	1.4	A
I_{SM}	peak source current	$T_{sp} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	5.6	A



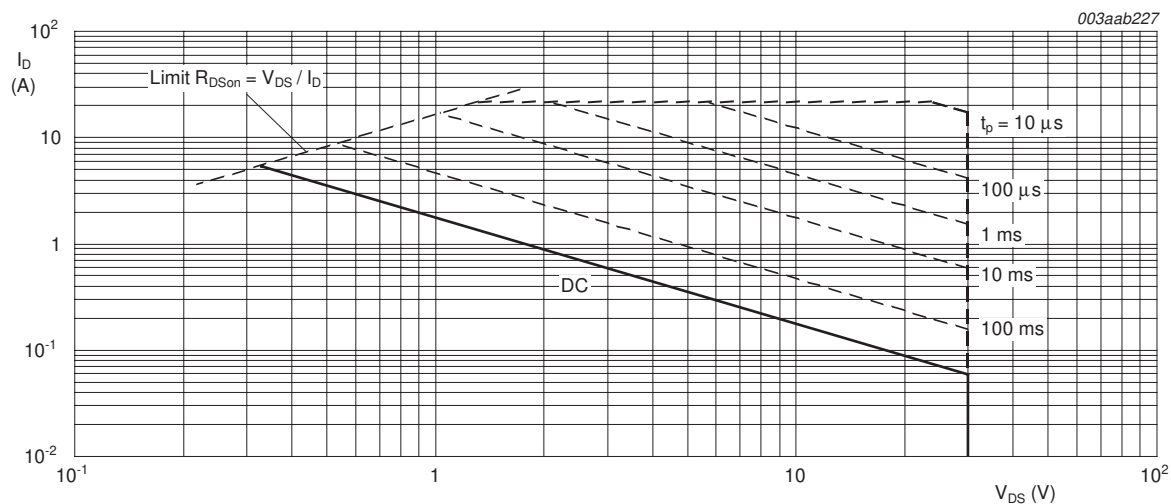
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

Fig 1. Normalized total power dissipation as a function of solder point temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized continuous drain current as a function of solder point temperature



T_{sp} = 25 °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	see Figure 4	-	-	70	K/W

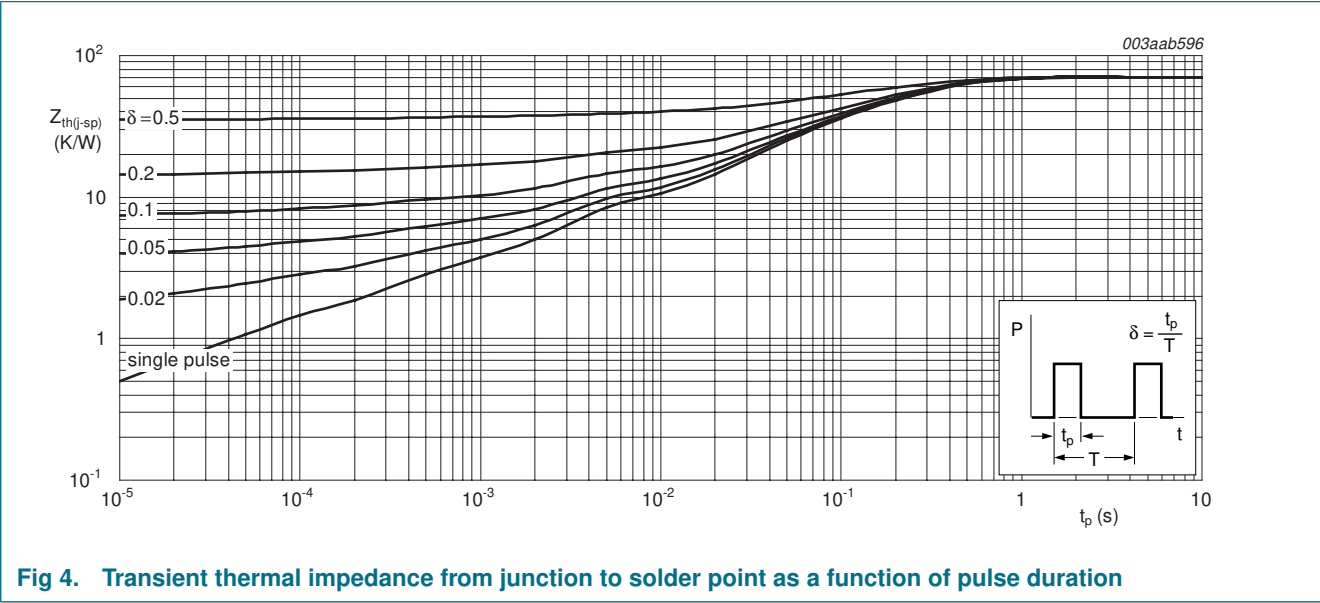


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration

6. Characteristics

Table 5. Characteristics
 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$; $V_{GS} = 0\text{ V}$				
		$T_j = 25\text{ }^{\circ}\text{C}$	30	-	-	V
		$T_j = -55\text{ }^{\circ}\text{C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}$; $V_{DS} = V_{GS}$; see Figure 9 and 10				
		$T_j = 25\text{ }^{\circ}\text{C}$	1	1.5	2	V
		$T_j = 150\text{ }^{\circ}\text{C}$	0.6	-	-	V
		$T_j = -55\text{ }^{\circ}\text{C}$	-	-	2.2	V
I_{DSS}	drain leakage current	$V_{DS} = 30\text{ V}$; $V_{GS} = 0\text{ V}$				
		$T_j = 25\text{ }^{\circ}\text{C}$	-	-	1	μA
		$T_j = 150\text{ }^{\circ}\text{C}$	-	-	100	μA
I_{GSS}	gate leakage current	$V_{GS} = \pm 20\text{ V}$; $V_{DS} = 0\text{ V}$	-	10	100	nA
R_G	gate resistance	$f = 1\text{ MHz}$; $V_{GSS(AC)} = 150\text{ mV}$	-	1.9	-	Ω
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 2\text{ A}$; see Figure 6 and 8				
		$T_j = 25\text{ }^{\circ}\text{C}$	-	40	47	m Ω
		$T_j = 150\text{ }^{\circ}\text{C}$	-	68	80	m Ω
		$V_{GS} = 4.5\text{ V}$; $I_D = 1.5\text{ A}$; see Figure 6 and 8	-	49	60	m Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 3\text{ A}$; $V_{DS} = 15\text{ V}$; $V_{GS} = 4.5\text{ V}$; see Figure 11 and 12	-	8.8	-	nC
Q_{GS}	gate-source charge		-	1.1	-	nC
Q_{GD}	gate-drain charge		-	1.6	-	nC
$V_{GS(pl)}$	gate-source plateau voltage		-	2.83	-	V
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 30\text{ V}$; $f = 1\text{ MHz}$; see Figure 14	-	350	-	pF
C_{oss}	output capacitance		-	100	-	pF
C_{rss}	reverse transfer capacitance		-	64.1	-	pF
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 0\text{ V}$; $f = 1\text{ MHz}$	-	570	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}$; $R_L = 15\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $R_G = 6\text{ }\Omega$	-	4.1	-	ns
t_r	rise time		-	4.3	-	ns
$t_{d(off)}$	turn-off delay time		-	12.9	-	ns
t_f	fall time		-	4.9	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 1.5\text{ A}$; $V_{GS} = 0\text{ V}$; see Figure 13	-	0.79	1.2	V
t_{rr}	reverse recovery time	$I_S = 2\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$	-	19.25	-	ns
Q_r	recovered charge		-	0.73	-	nC

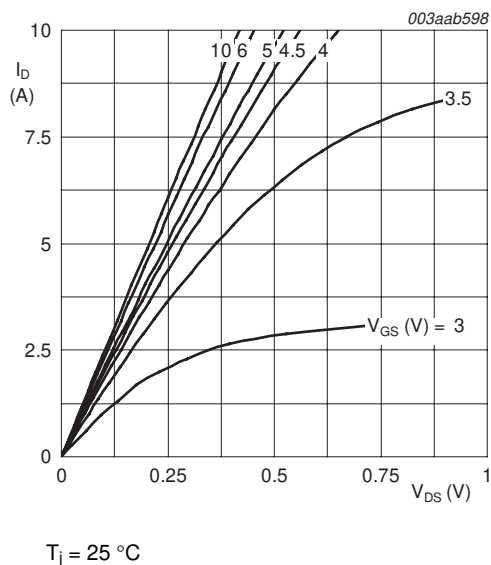


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

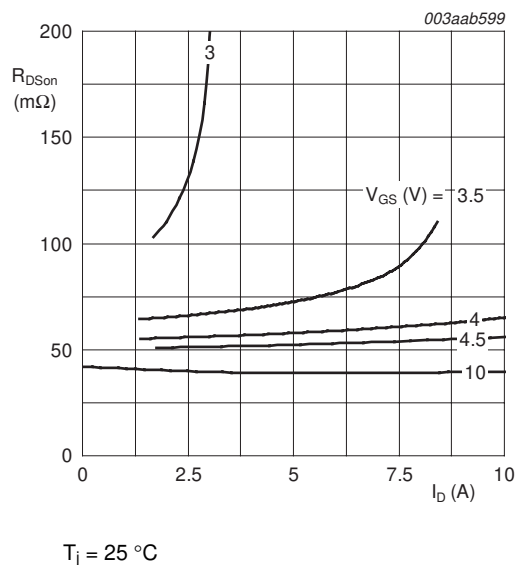


Fig 6. Drain-source on-state resistance as a function of drain current; typical values

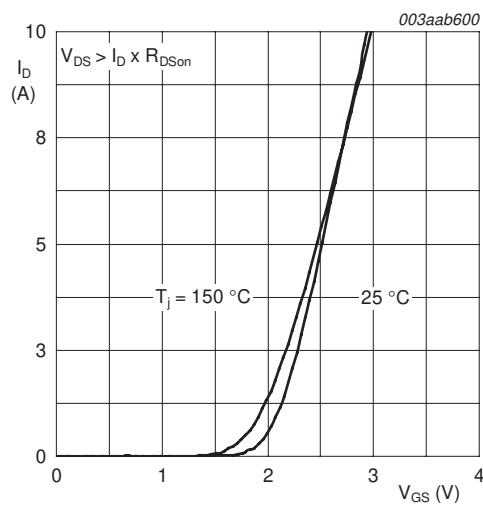


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

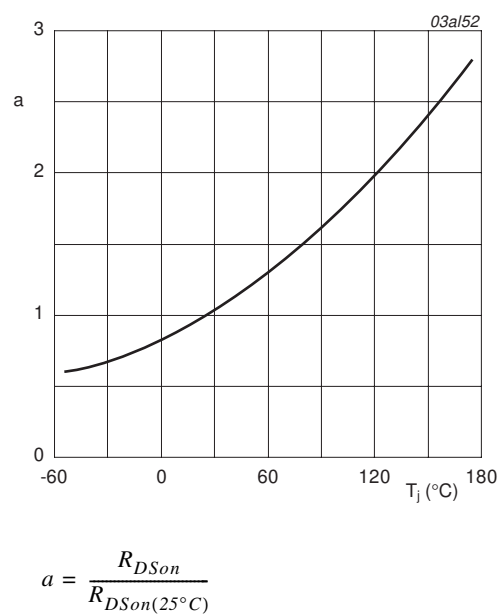
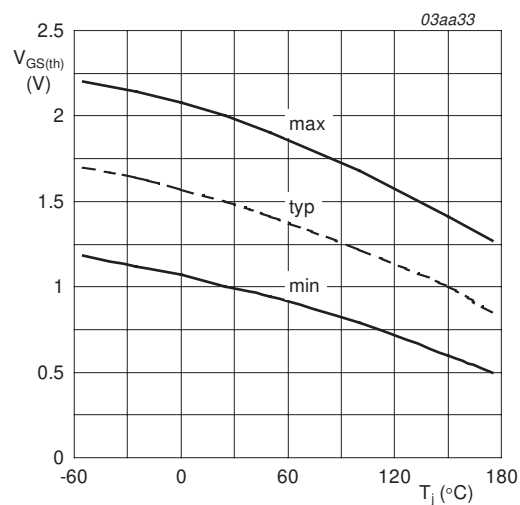
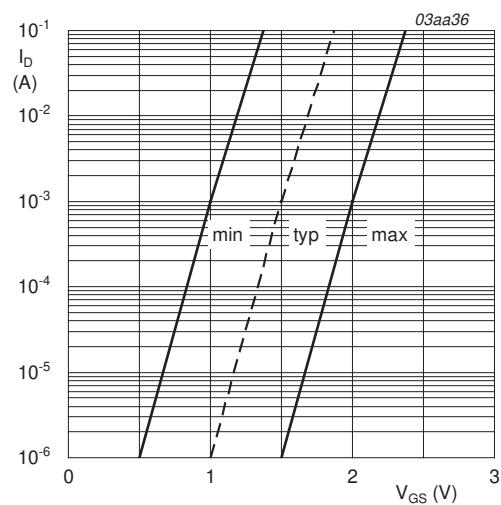


Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature



$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature



$T_j = 25 \text{ °C}$; $V_{DS} = 5 \text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

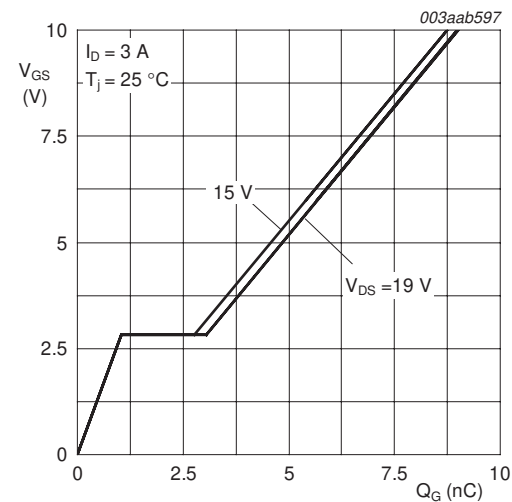


Fig 11. Gate-source voltage as a function of gate charge; typical values

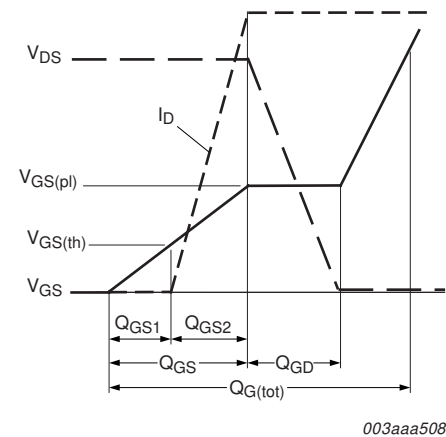
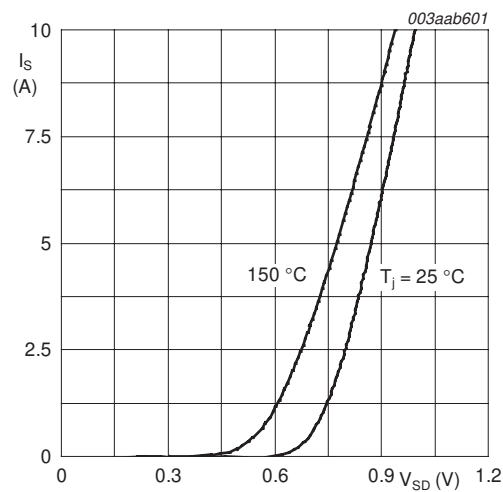
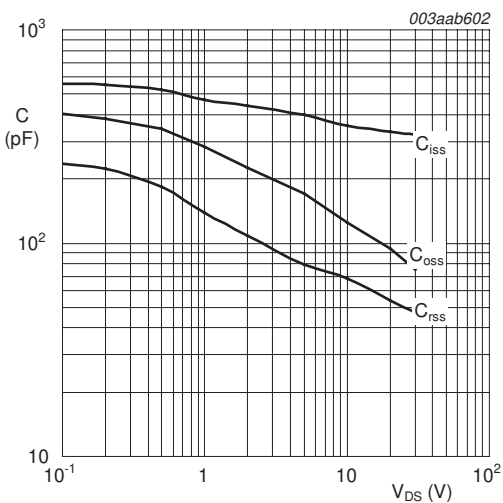


Fig 12. Gate charge waveform definitions



$T_j = 25\text{ °C}$ and 150 °C ; $V_{GS} = 0\text{ V}$

Fig 13. Source current as a function of source-drain voltage; typical values



$V_{GS} = 0\text{ V}$; $f = 1\text{ MHz}$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

7. Package outline

Plastic surface-mounted package (TSOP6); 6 leads SOT457

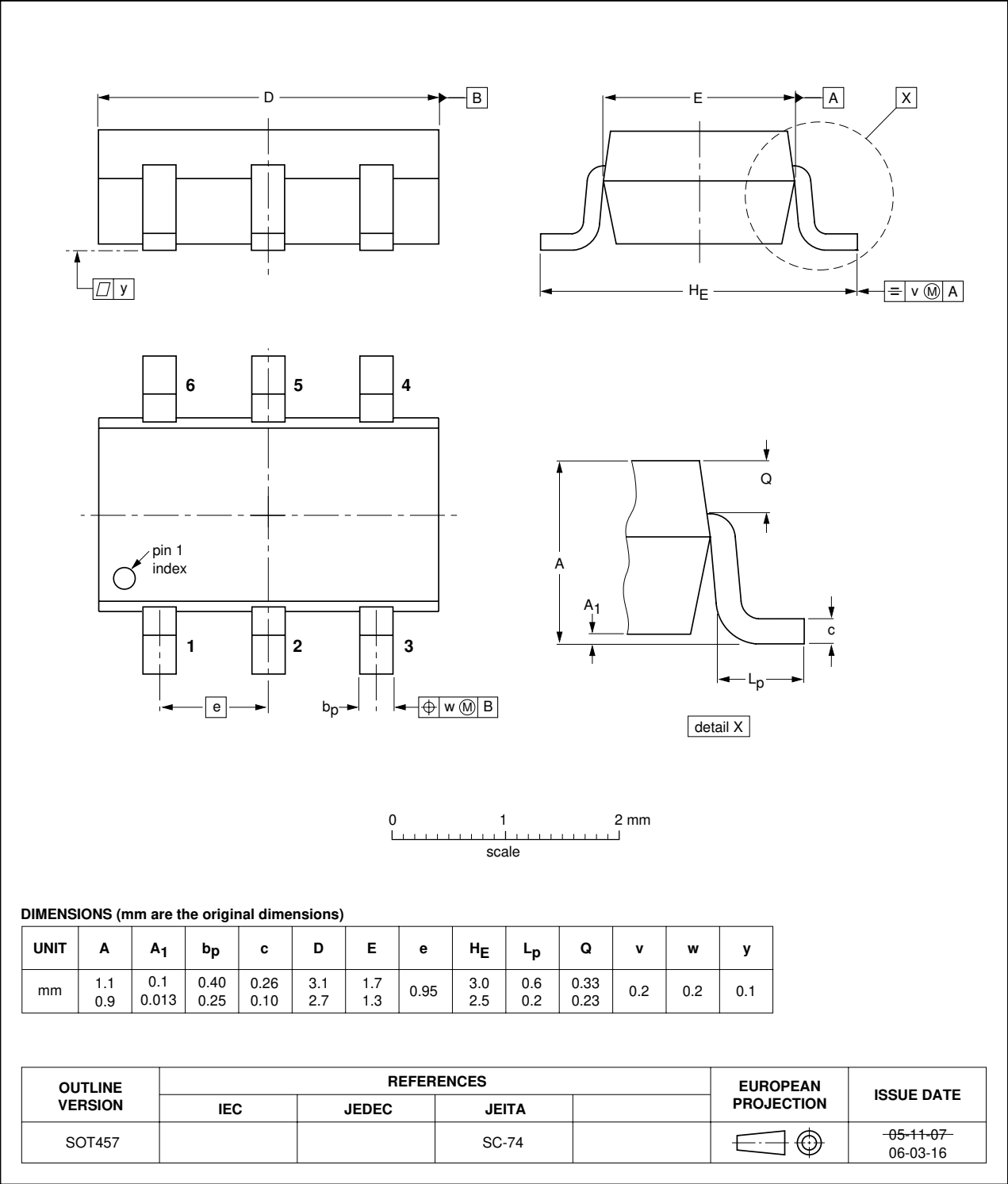


Fig 15. Package outline SOT457 (TSOP6)

8. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMN49EN_1	20070413	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

9.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

9.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of a NXP Semiconductors product can reasonably be expected to

result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

9.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

TrenchMOS — is a trademark of NXP B.V.

10. Contact information

For additional information, please visit: <http://www.nxp.com>

For sales office addresses, send an email to: salesaddresses@nxp.com

11. Contents

1 Product profile 1

1.1 General description..... 1

1.2 Features 1

1.3 Applications 1

1.4 Quick reference data..... 1

2 Pinning information..... 1

3 Ordering information..... 2

4 Limiting values..... 2

5 Thermal characteristics..... 4

6 Characteristics..... 5

7 Package outline 9

8 Revision history..... 10

9 Legal information..... 11

9.1 Data sheet status 11

9.2 Definitions..... 11

9.3 Disclaimers..... 11

9.4 Trademarks..... 11

10 Contact information..... 11

11 Contents 12



Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.